







Opportunities and Obstacles of Monolithic III-V Integration on Silicon

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The future of data processing



Cisco Trends:

- The amount of VoD traffic in 2020 will be equivalent to 7.2 billion DVDs per month.
- Virtual reality traffic quadrupled in 2015
- The number of devices connected to IP networks will be more than three times the global population by 2020

• Energy sustainability

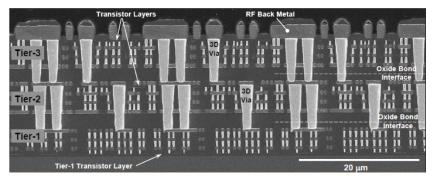
- Heat losses in datacenters
- Heat losses in smartphones and computers







Towards 3D hybrid microprocessors



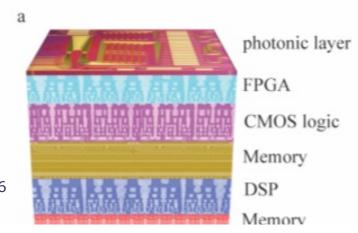
3D electronic architectures
Substrate removal integration
(coming from GPU)

MIT Lincoln lab (2013)

Hardware and functional hybridization

- different functionalities(memory, routing, computing)
- different technologies (photonics?)
- different computation paradigms

Integrated lasers on Silicon, Elsevier 2016





- on-chip optical waveguides for visible and IR wavelengths
- detectors
- modulators
- advanced components (filters, AWG etc...)
- on chip lasers









III-V is the only mature laser platform



Xiophotonics.com



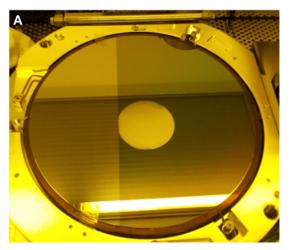
III-V integration methods

Wafer bonding

Fastest time to market?

Full wafers

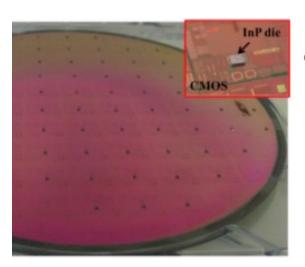
Scalability issue
Gas by-products evacuation



Luo et al. Front. Mater. 2015

Small die bonding

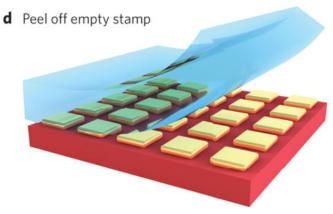
Reproducibility



CEA-Leti

Massive transfer Printing

III-V coupons on Stamps
Scalability and accurate positioning



B. Corbett's group



III-V integration methods

Monolithic integration: direct gowth of III-V on Si

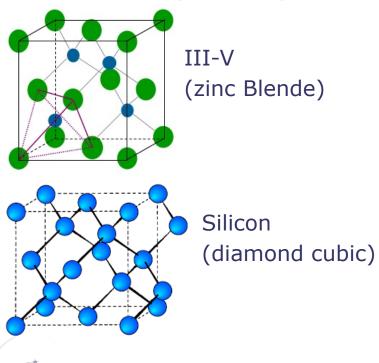
Cheaper,

Foton

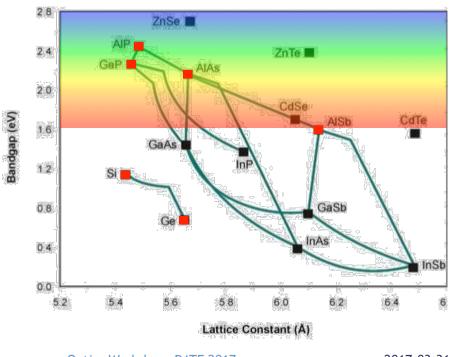
Straightforward scalability

But can it be mature?

Polar on non-polar crystals



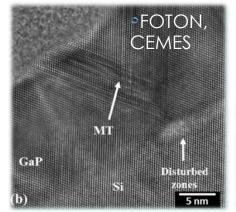
Lattice mismatch

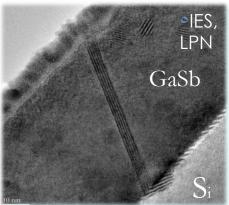


Polar on non-polar defects

➤ Surface preparation

Cross TEM





Y. Ping Wang et al., Appl. Phys. Lett.107, 191603 (2015)

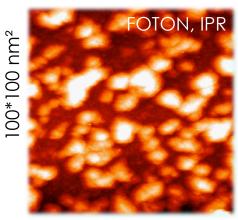
- Defects induced by pollution of the substrates
- Advanced substrate preparation
- microtwins: rotations of the III-V crystal
- no optoelectronic characterization

Huge roughness

not the only problem

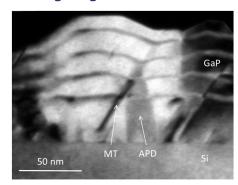
➤ 3D nucleation

STM of the nucleation layer



3nm GaP/Si-6°off

Cross TEM after 100nm of nonmanaged growth

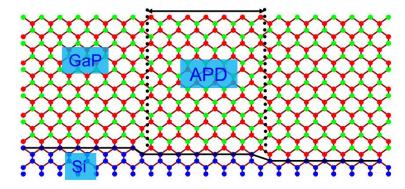




Polar on non-polar defects

Antiphase domains

- bi-stepped surface -> vicinal surbstrates
- Initial Ga or P coverage



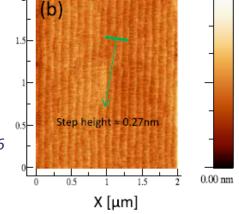
Wafer preparation

○ LTM

Foton

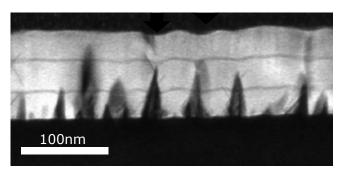
- GaAs/Si
- Vicinal to nominal

Alcotte et al. APL Mater. 2016

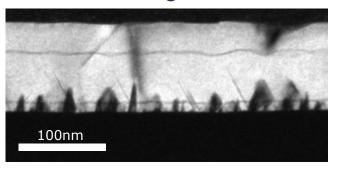


1.50 nm

➤ Annihilation layers



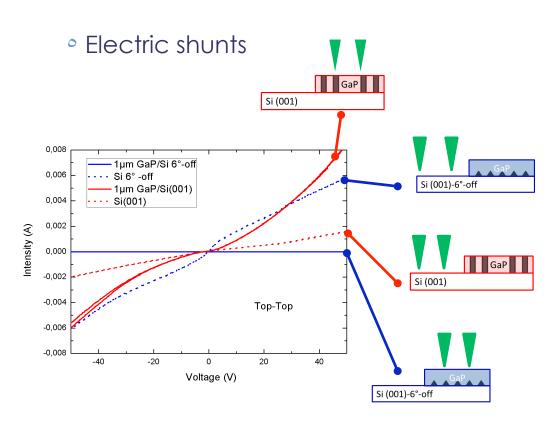
- GaP/Si
- Al-Rich layers to control the annhiliation height



Antipode ANR

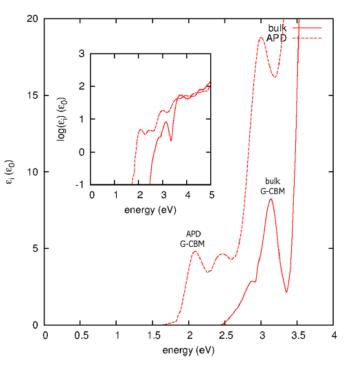
Polar on non-polar defects

➤ Antiphase domains opto-electronic impact



Antipode ANR



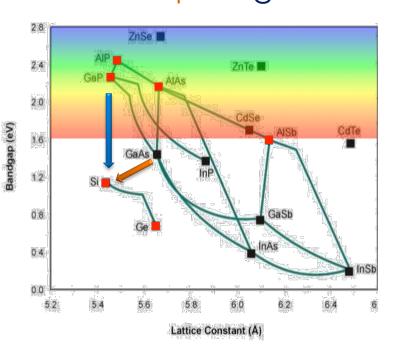


Tea et al. J. Appl. Phys. 2014

interesting for nonlinear optics

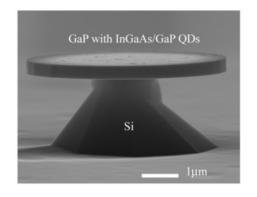


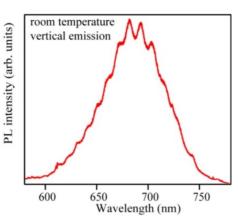
pseudomorphic and metamorphic growth



➤ GaP/Si emitters

- QDs 100nm above Si interface
- room temperature emission



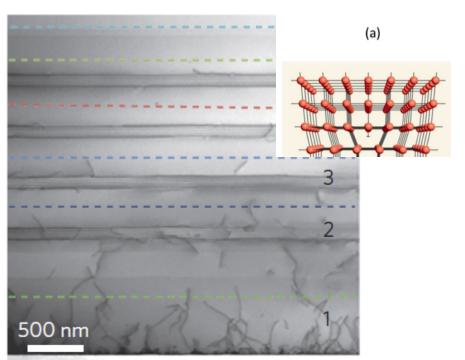


➤ Huge advances on GaAs/Si devices!



GaAs metamorphic integration

Threading dislocation management

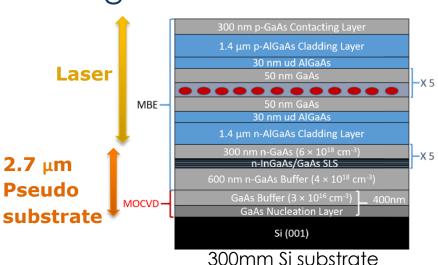


Chen et al. Nature Phot. 2016

- Strained layer Superlattice
- Requires a thick buffer
- Lifetime issue

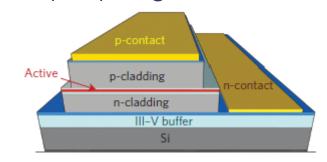


CMOS compatible design

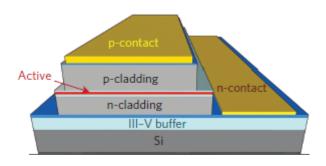


Chen et al. Opt. Express 2017

Top-top ridge laser

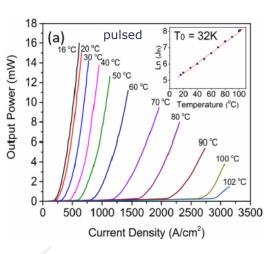


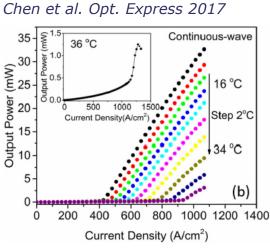
GaAs/Si laser performances



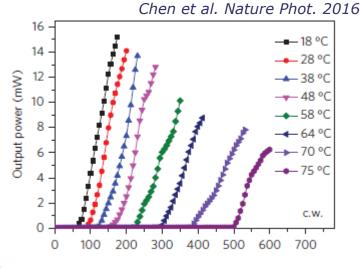
- Large temperature span
- state-of-the-art thresholds
- long lifetime

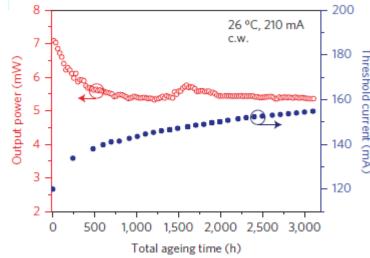
On nominal 300mm Si





On vicinal Si







- Defect management for III-V/Si integration becomes mature
- GaAs/Si lasers reach state-of-the-art performances
 - smaller consumption than InP-based lasers
 - Si transparency emission
 - promising lifetimes
- Remaining issue of the pseudo-substrate
 - Interest of SOI integration?
 - 3D integration (substrate removal)



Acknowledgements

•Colleagues from 3D core:

- Sebastien Le Beux
- Olivier Sentieys
- Daniel Chillet
- C. Cornet
- C. Killian
- C. Peucheret
- A. Parini
- P. Besnard
- R. tremblay
- J. Juo





ANR-14-CE26-0014





